

## R-C Thermal Model Parameters

### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

*For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	18.5848	N/A	13.0481
RT2	7.4064	N/A	11.2706
RT3	20.4057	N/A	9.0038
RT4	73.2996	N/A	4.7028
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	31.4157 m	N/A	38.5072 m
CT2	2.2120 m	N/A	4.3348 m
CT3	150.3018 m	N/A	256.6742 m
CT4	1.2225	N/A	123.2009 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ( $^{\circ}\text{C}/\text{W}$ )			
Junction to	Ambient	Case	Foot
RF1	3.6346	N/A	4.9247
RF2	17.6426	N/A	16.4513
RF3	28.4869	N/A	15.6115
RF4	69.7394	N/A	1.0504
Thermal Capacitance (Joules/ $^{\circ}\text{C}$ )			
Junction to	Ambient	Case	Foot
CF1	490.1778 u	N/A	2.1669 m
CF2	10.5969 m	N/A	5.6969 m
CF3	62.9692 m	N/A	58.9766 m
CF4	1.1937	N/A	7.4953

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

